

**Abstract****A BURIED HETERO-STRUCTURE InP-BASED  
OPTO-ELECTRONIC DEVICE WITH NATIVE  
OXIDIZED CURRENT BLOCKING LAYER**

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A buried hetero-structure InP-based opto-electronic device with native oxidized current blocking layer comprises a InP semiconductor substrate, a buffer layer, a ridge mesa containing lower confinement layer, active layer  
10 and upper grating confinement layer, a first InP cladding layer and a native oxidized Al-bearing layer as current blocking layers at both lateral edges, a second InP cladding layer, contact layer, contact metal, and the second ridge mesa covered with insulating layer. This method is to facilitate the processing of conventional buried hetero-structure InP-based opto-  
15 electronic device.

FIG. 2f



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